

Abstract

An etching method according to the present disclosure includes: providing a substrate having SiGe or Ge on a surface portion thereof into a chamber; supplying an etching gas for etching SiGe or Ge to a substrate retained at a first temperature at which an etching reaction does not occur, and causing the etching gas to be adsorbed to the surface of the substrate; and setting the temperature of the substrate to a second temperature at which a reaction between the SiGe or the Ge and the etching gas occurs, and etching the SiGe or Ge.